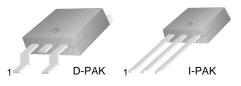


MJD117

D-PAK for Surface Mount Applications

- High DC Current Gain
- Built-in a Damper Diode at E-C
- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I-PAK, " I " Suffix)
- Electrically Similar to Popular TIP117

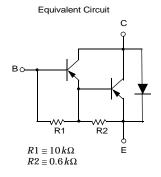


1.Base 2.Collector 3.Emitter

PNP Silicon Darlington Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CBO}	Collector-Base Voltage	- 100	- 100 V	
V _{CEO}	Collector-Emitter Voltage	- 100	V	
V _{EBO}	Emitter-Base Voltage	- 5	V	
I _C	Collector Current (DC)	- 2	Α	
I _{CP}	Collector Current (Pulse)	- 4	Α	
I _B	Base Current	- 50	mA	
P _C	Collector Dissipation (T _C =25°C)	20	W	
	Collector Dissipation (T _a =25°C)	1.75	W	
T_J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 65 ~ 150	°C	



Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V _{CEO} (sus)	*Collector-Emitter Sustaining Voltage	$I_C = -30 \text{mA}, I_B = 0$	- 100		V
I _{CEO}	Collector Cut-off Current	$V_{CE} = -50V, I_{B} = 0$		- 20	μΑ
I _{CBO}	Collector Cut-off Current	V _{CB} = - 100V, I _E = 0		- 20	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$		- 2	mA
h _{FE}	*DC Current Gain	$V_{CE} = -3V, V_{EB} = -0.5A$ $V_{CE} = -3V, V_{EB} = -2A$ $V_{CE} = -3V, I_{C} = -4A$	500 1000 200	12K	
V _{CE} (sat)	*Collector-Emitter Saturation Voltage	I _C = -2A, I _B = -8mA I _C = -4A, I _B = -40mA		- 2 - 3	V V
V _{BE} (sat)	*Base-Emitter Saturation Voltage	I _C = - 4A, I _B = - 40mA		- 4	V
V _{BE} (on)	*Base-Emitter ON Voltage	V _{CE} = - 3A, I _C = - 2A		- 2.8	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -10V, I_{C} = -0.75A$	25		MHz
C _{ob}	Output Capacitance	$V_{CB} = -10V, I_{E} = 0$ f= 0.1MHz		200	pF

^{*} Pulse Test: PW≤300μs, Duty Cycle≤2%

Typical Characteristics

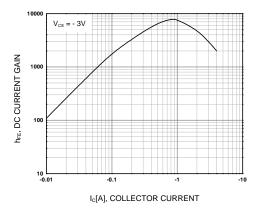


Figure 1. DC current Gain

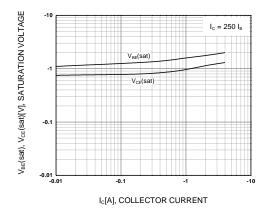


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

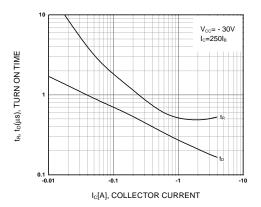


Figure 3. Collector Output Capacitance

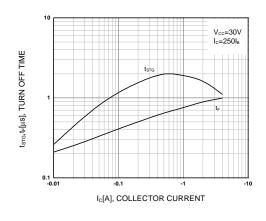


Figure 4. Turn On Time

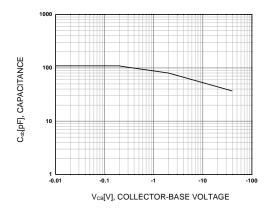


Figure 5. Turn Off Time

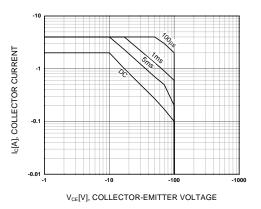


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

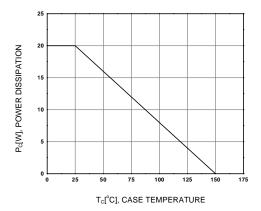
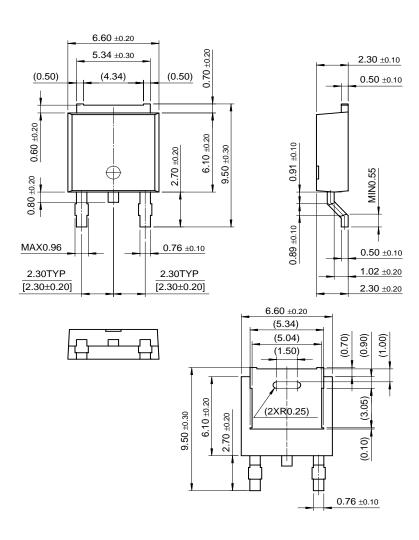


Figure 7. Power Derating

Package Demensions

D-PAK



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